



CHENMKO ENTERPRISE CO.,LTD

CH761UPT

Lead free devices

SURFACE MOUNT

SCHOTTKY BARRIER DIODE

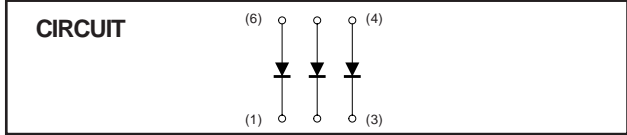
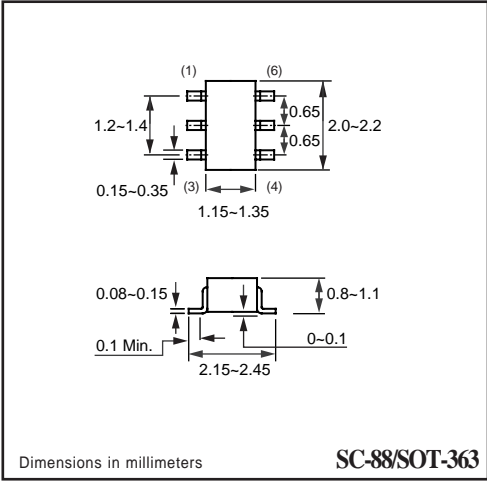
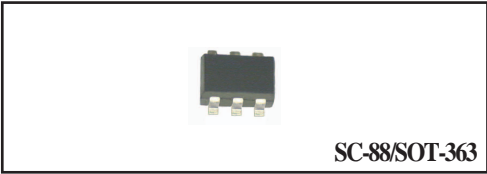
VOLTAGE 12 Volts CURRENT 0.1 Ampere

APPLICATION
* Low voltage high speed switching application

FEATURE
* Small surface mounting type. (SC-88/SOT-363)
* Low VF and low IR
* Three diodes in parallel installation
* Power dissipation is 200mW
* Maximum peak forward current is 200mA

CONSTRUCTION
* Silicon epitaxial planar

MARKING
* JB



MAXIMUM RATINGS (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	CH761UPT	UNITS
Maximum Recurrent Peak Reverse Voltage	VRRM	12	Volts
Maximum RMS Voltage	VRMS	8	Volts
Maximum DC Blocking Voltage	VDC	12	Volts
Maximum Average Forward Rectified Current	Io	0.1	Amps
Peak Forward Surge Current at 8.3 mSec single half sine-wave	IFSM	1.0	Amps
Typical Junction Capacitance between Terminal (Note 1)	CJ	30	pF
Operating Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	TSTG	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	CH761UPT			UNITS
		MIN.	TYP.	MAX.	
Maximum Instantaneous Forward Voltage at IF= 1mA IF= 5mA IF= 100mA	VF	-	0.16	-	Volts
		-	0.20	0.28	
		-	0.32	0.50	
Maximum Average Reverse Current at VR= 20V	IR	-	-	20	uAmps

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 0 volts.
2. ESD sensitive product handling required.

RATING CHARACTERISTIC CURVES (CH761UPT)

FIG. 1 FORWARD CHARACTERISTICS

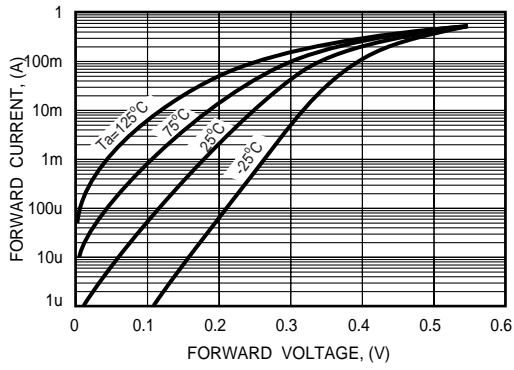


FIG. 2 - REVERSE CHARACTERISTICS

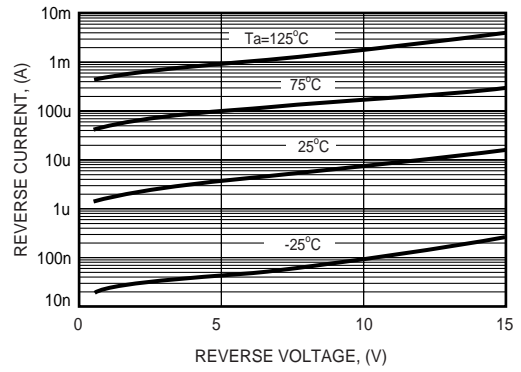


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

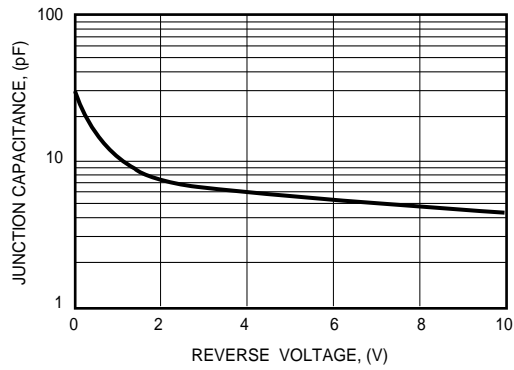


FIG. 4 - TYPICAL FORWARD CURRENT DERATING CURVE

